



APT6018LNR 600V 35.0A 0.18Ω

AVALANCHE RATED

N-CHANNEL ENHANCEMENT MODE HIGH VOLTAGE POWER MOSFETS

MAXIMUM RATINGS All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Parameter	A	APT6018LNR	UNIT		
V _{DSS}	Drain-Source Voltage		600	Volts		
I _D	Continuous Drain Current @ T _C = 25°C		> 35			
IDM	Pulsed Drain Current 10		140	Amps		
V _{GS}	Gate-Source Voltage Continuous	±20	Volts			
V _{GSM}	Gate-Source Voltage Transient	±30				
P _D	Total Power Dissipation @ T _C = 25°C	520		Watts		
' D	Linear Derating Factor	4.1	6	W/°C		
T_{J}, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150		- °C		
TL	Lead Temperature: 0.063" from Case for 10 Sec.	300				
I _{AR}	Avalanche Current (Repetitive and Non-Repetitive)	35	Amps			
E _{AR}	Repetitive Avalanche Energy 1	50				
E _{AS}	Single Pulse Avalanche Energy	250	— mJ			

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number		MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage (V _{GS} = 0V, I _D = 250 μA)		600			Volts
I _D (ON)		APT6018LNR	35			Amps
	$(V_{DS} > I_{D}(ON) \times R_{DS}(ON) \text{ Max, } V_{GS} = 10V)$					
R _{DS} (ON)	Drain-Source On-State Resistance	APT6018LNR			0.18	
	(V _{GS} = 10V, 0.5 l _D [Cont.])					Ohms
I _{DSS}	Zero Gate Voltage Drain Current (V _{DS} = V _{DSS} , V _{GS} = 0V)				250	
	Zero Gate Voltage Drain Current (V _{DS} = 0.8 V _{DSS} , V _{GS} = 0V, T _C = 125°C)				1000	μА
I _{GSS}	Gate-Source Leakage Current (V _{GS} = ±20V, V _{DS} = 0V)			· · · · · · · · · · · · · · · · · · ·	±100	nA
V _{GS} (TH)	Gate Threshold Voltage $(V_{DS} = V_{GS'} _{D} = 2.5mA)$		2		4	Volts

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	ТҮР	MAX	UNIT
R _{eJC}	Junction to Case			0.24	
R _{eja}	Junction to Ambient			40	°C/W

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

USA

405 S.W. Columbia Street EUROPE

Bend, Oregon 97702-1035 Phone: (503) 382-8028 FAX: (503) 388-0364

Avenue J.F. Kennedy Bât B4 Parc Cadéra Nord F-33700 Merignac - France Phone: (33) 56 34 34 71 FAX: (33) 56 47 97 61

Page 102

DYNAMIC CHARACTERISTICS

APT6018LNR

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C _{iss}	Input Capacitance	V _{GS} = 0V		7800		pF
C _{oss}	Output Capacitance	V _{DS} = 25V		850		
C _{rss}	Reverse Transfer Capacitance	f = 1 MHz		525		
Qg	Total Gate Charge ③	V _{GS} = 10V		290		nC
\mathbf{Q}_{gs}	Gate-Source Charge	$V_{DD} = 0.5 V_{DSS}$		35		
Q_{gd}	Gate-Drain ("Miller") Charge	I _D = I _D [Cont.] @ 25°C		125		
t _d (on)	Turn-on Delay Time	V _{GS} = 15V		20		
t _r	Rise Time	$V_{DD} = 0.5 V_{DSS}$		40		
t _d (off)	Turn-off Delay Time	$I_D = I_D [Cont.] @ 25^{\circ}C$ $R_G = 1.8\Omega$		130	-	ns
t,	Fall Time	$R_G = 1.8\Omega$	A	75		1

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number	MIN	ТҮР	MAX	UNIT
I _s	Continuous Source Current (Body Diode)	ART6018LNR		35	
l _{sm}	Pulsed Source Current (1) (Body Diode)	APT6018LNR		140	Amps
V _{SD}	Diode Forward Voltage (V _{GS} = 0V, I _S = -I _D (Cont.))			1.3	Volts
t rr	Reverse Recovery Time (I _S = -I _D [Cont.], dI _S /dt = 100A		650		ns
Qrr	Reverse Recovery Charge (I _S = -I _D [Cont.], dig dt = 10	DA/μs)	18		μС

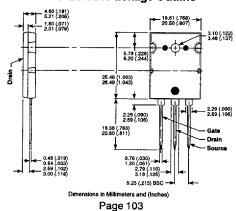
SAFE OPERATING AREA CHARACTERISTICS

Symbol	Characteristic Pest Conditions / Part Number			TYP	MAX	UNIT		
SOA1	Safe Operating Area $V_{DS} = 0.4 V_{DSS}$, $I_{DS} = P$	_D / 0.4 V _{DSS} , t = 1 Sec.	520					
SOA2	Safe Operating Area $I_{DS} = I_{D}$ [Cont.], $V_{DS} = P$	$_{\rm D}$ / I $_{\rm D}$ [Cont.], t = 1 Sec.	520			Watts		
I _{LM}	Inductive Current Clamped APT6018LNR		140	 		Amna		
						Amps		

① Repetitive Rating: Pulse width limited by maximum junction temperature.

APT Reserves the right to change, without notice, the specifications and information contained herein.

TO-264AA Package Outline



■ 0257909 0001507 T27 ■

³ See MIL-STD-750 Method 3471

 $[\]textcircled{4}$ Starting T $_{j}$ = +25°C, L = 4.08mH, R $_{G}$ = 25 $\!\Omega,$ Peak I $_{L}$ = 35 A

 $[\]textcircled{2}$ Pulse Test: Pulse width < 380 μ S, Duty Cycle < 2%